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ABSTRACT

10       Apparatus for the processing of materials involving  
placing a material either placed between an radio-frequency  
electrode and a ground electrode, or which is itself one of  
the electrodes. This is done in atmospheric pressure  
conditions. The apparatus effectively etches or cleans  
15 substrates, such as silicon wafers, or provides cleaning of  
spools and drums, and uses a gas containing an inert gas and  
a chemically reactive gas.

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